

SOLAR

InOx EB
InOxSide EB

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The emitter etch back series

The InOxSide ensures efficient junction isolation and PSG removal for high throughput solar cell production. With the additional emitter etch back step, the EB series offers an extra boost in blue response and improves cell efficiency as well as process reliability. Together with the RENA InDop system, the InOxSide EB takes the performance of inline diffusion to the level of POCl_3 -diffusion.

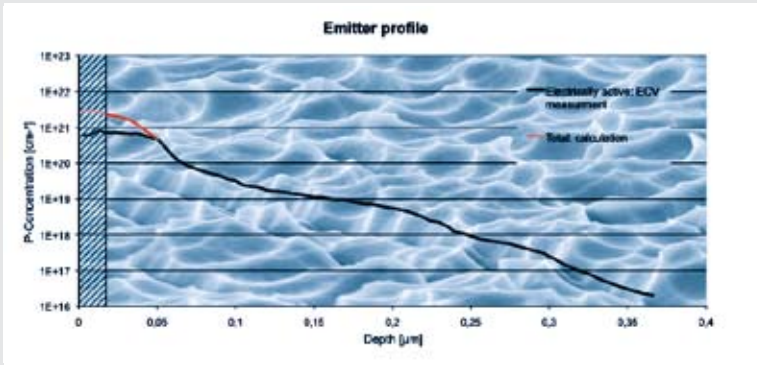
Areas of application

- InOx EB: PSG removal and emitter etch back
- InOxSide EB: PSG removal, junction isolation and emitter etch back
- Designed for multi- and monocrystalline wafers, INLINE and POCl_3 -diffusion
- Wafer transfer systems available for automatic loading and unloading

Features and benefits

- PSG removal, junction isolation and emitter etch back in one single tool
 - Optimised footprint
 - Ideal process and work flow integration
- Technological leadership
 - Advanced process integration with the RENA InDop system offers a further efficiency increase and raises the performance of inline diffusion to the level of POCl_3 -diffusion
 - Process start up by RENA
 - Low total cost of ownership
 - Stable and reproducible processing





Front view InOxSide EB

Technical Data InOx EB, InOxSide EB

	InOx EB, InOxSide EB ST	InOx EB, InOxSide EB HT
	• 5 lanes for 156 mm wafers	• 5 lanes for 156 mm wafers
Process InOx EB	Inline PSG removal and emitter etch back	
Process InOxSide EB	Inline PSG removal, junction isolation and emitter etch back	
Dimensions InOx EB	7800 x 2150 x 2350 mm (length x width x height)	10800 x 2150 x 2350 mm (length x width x height)
Dimensions InOxSide EB	12000 x 2150 x 2350 mm (length x width x height)	16200 x 2150 x 2350 mm (length x width x height)
Throughput	1875 wafers/h gross • wafer size 156 mm	3000 wafers/h gross • wafer size 156 mm
Wafer thickness	> 150 µm	> 150 µm